8205SA/W

N-Channel Trench Power MOSFET

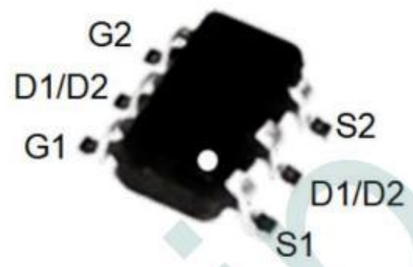
RDS(ON)=20.0mΩ (Typ.) @ VGS =4.5V

RDS(ON)=26.0mΩ (Typ.) @ VGS =2.5V

Application

- LCD TV
- Notebook
- Elevator
- Inductive heating
- Power tools

Package



Pin Description

SOT23-6

Absolute Max Ratings at Ta=25℃ (Note1)

Parameter	Symbol	Maximum	Units
Drain to Source Voltage	VDSS	15	V
Gate to Source Voltage	VGSS	±12	V
Drain Current-Continuous	ID	5	A
Drain Current (Pulse)	IDM	16	A
Maximum Power Dissipation	PD	1.9	W
Junction Temperature	TJ	150	°C
Storage Temperature	TSTG	-55 to +150	°C

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

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